

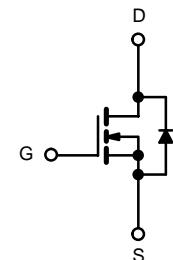
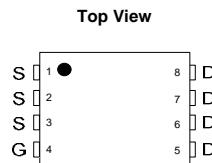
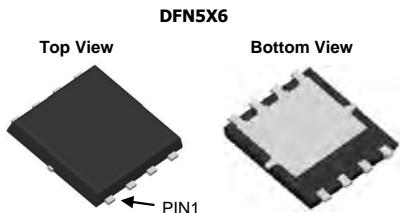
# NCE0160G-VB Datasheet

## N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.009 at $V_{GS} = 10$ V	65

### FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 %  $R_g$  Tested



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 150$ °C)	$T_C = 25$ °C	65	A
	$T_C = 70$ °C	60	
	$T_A = 25$ °C	20 <sup>b, c</sup>	
	$T_A = 70$ °C	18.5 <sup>b, c</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	180	
Continuous source-drain diode current	$T_C = 25$ °C	60	
	$T_A = 25$ °C	4.8 <sup>b, c</sup>	
Single pulse avalanche current	$I_{AS}$	30	mJ
Single pulse avalanche energy	$E_{AS}$	40	
Maximum power dissipation	$T_C = 25$ °C	80	W
	$T_C = 70$ °C	50	
	$T_A = 25$ °C	5 <sup>b, c</sup>	
	$T_A = 70$ °C	3.2 <sup>b, c</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>c</sup>		260	

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	$R_{thJA}$	20	25	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	1.6	2	

#### Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c.  $t = 10$  s

**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

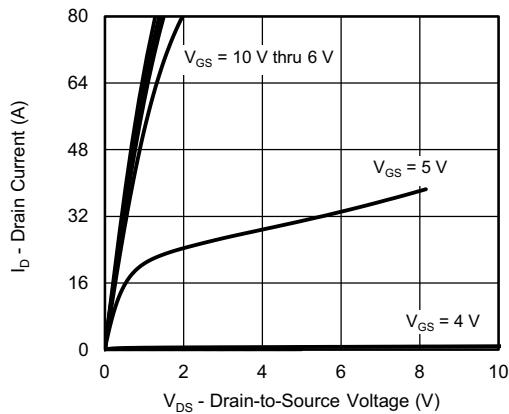
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	100	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10 \text{ mA}$	-	81	-	$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ temperature coefficient	$\Delta V_{GS(\text{th})}/T_J$	$I_D = 250 \mu\text{A}$	-	-7.5	-	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	3	-	5	V
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$	-	-	100	$\text{nA}$
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 100 \text{ V}$ , $V_{GS} = 0 \text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 70^\circ\text{C}$	-	-	15	
On-state drain current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 10 \text{ V}$ , $V_{GS} = 10 \text{ V}$	40	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$	-	0.009	-	$\Omega$
		$V_{GS} = 7.5 \text{ V}$ , $I_D = 10 \text{ A}$	-	0.012	-	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 10 \text{ A}$	-	46	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{iss}$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	-	3970	-	$\text{pF}$
Output capacitance	$C_{oss}$		-	132	-	
Reverse transfer capacitance	$C_{rss}$		-	11.2	-	
Total gate charge	$Q_g$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$	-	20	-	$\text{nC}$
Gate-source charge	$Q_{gs}$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 7.5 \text{ V}$ , $I_D = 10 \text{ A}$	-	15	-	
Gate-drain charge	$Q_{gd}$		-	6.45	-	
Output charge	$Q_{oss}$		-	3.5	-	
Gate resistance	$R_g$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 0 \text{ V}$	-	22	-	$\Omega$
Turn-on delay time	$t_{d(\text{on})}$	$f = 1 \text{ MHz}$  $V_{DD} = 50 \text{ V}$ , $R_L = 5 \Omega$ , $I_D \geq 10 \text{ A}$ , $V_{GEN} = 10 \text{ V}$ , $R_g = 1 \Omega$	0.2	0.76	1.4	
Rise time	$t_r$		-	12	24	
Turn-off delay time	$t_{d(\text{off})}$		-	5	10	
Fall time	$t_f$		-	19	38	
Turn-on delay time	$t_{d(\text{on})}$		-	5	10	
Rise time	$t_r$		-	15	30	
Turn-off delay time	$t_{d(\text{off})}$		-	6	12	
Fall time	$t_f$		-	19	38	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	$T_C = 25^\circ\text{C}$  $I_F = 10 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$	-	-	60	$\text{A}$
Pulse diode forward current	$I_{SM}$		-	-	80	
Body diode voltage	$V_{SD}$		-	0.78	1.1	V
Body diode reverse recovery time	$t_{rr}$		-	43	86	ns
Body diode reverse recovery charge	$Q_{rr}$		-	72	144	$\text{nC}$
Reverse recovery fall time	$t_a$		-	33	-	
Reverse recovery rise time	$t_b$		-	10	-	

**Notes**

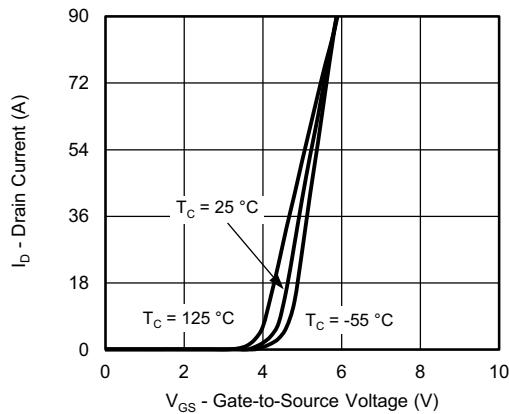
a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

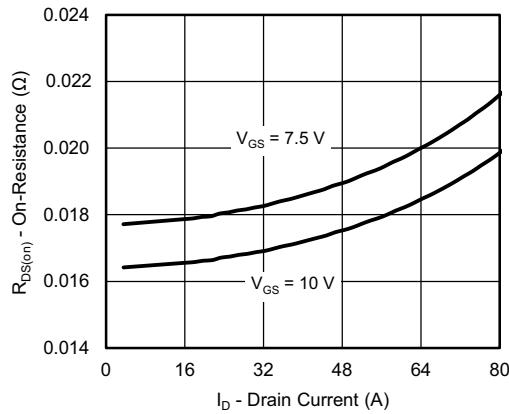
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



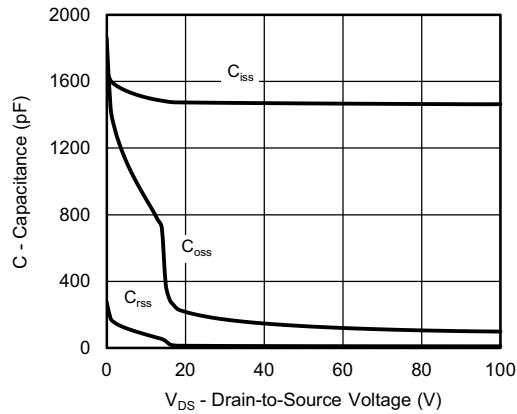
Output Characteristics



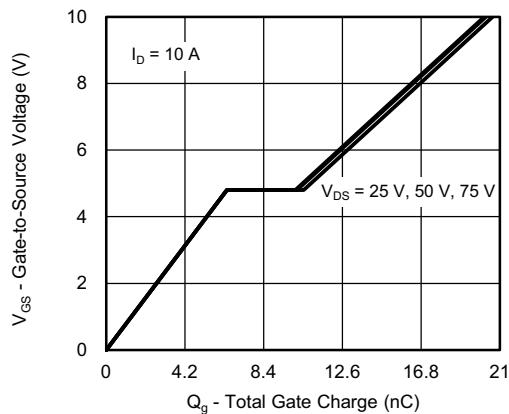
Transfer Characteristics



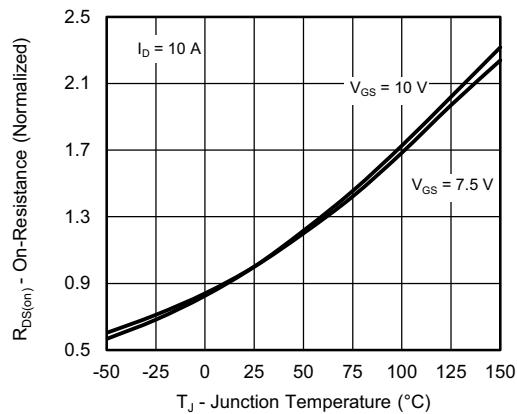
On-Resistance vs. Drain Current and Gate Voltage



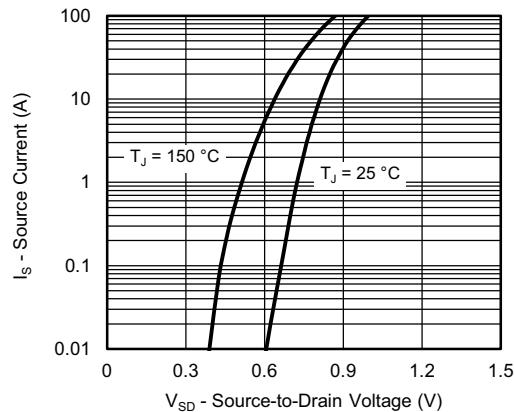
Capacitance



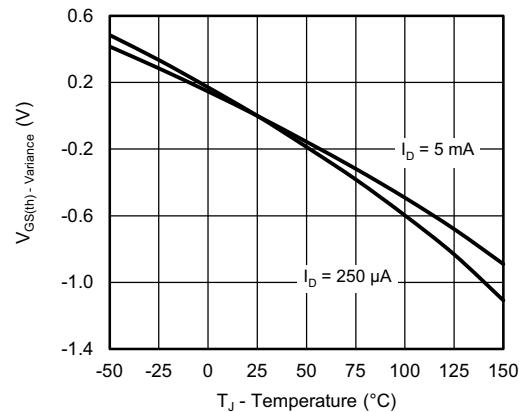
Gate Charge



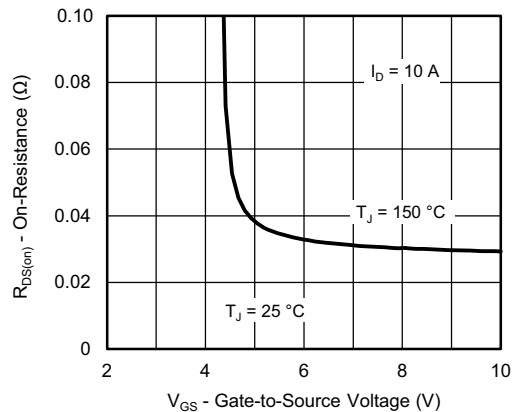
On-Resistance vs. Junction Temperature

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


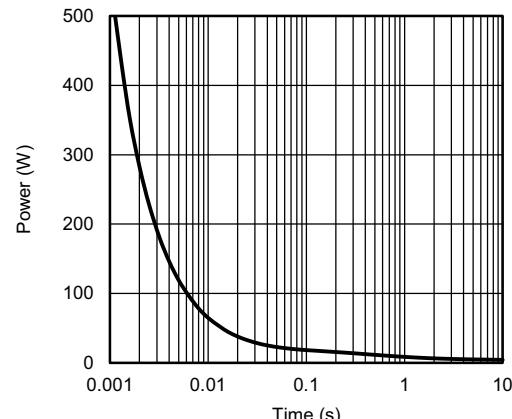
Source-Drain Diode Forward Voltage



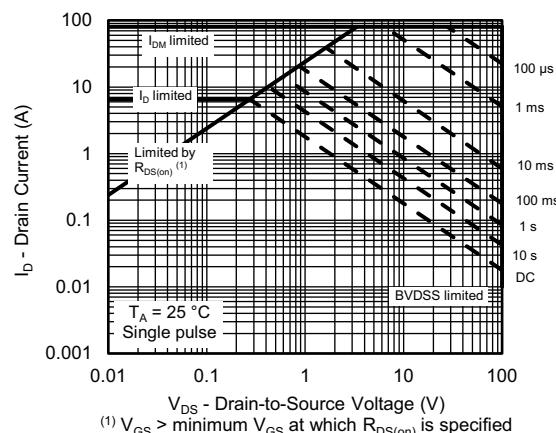
Threshold Voltage



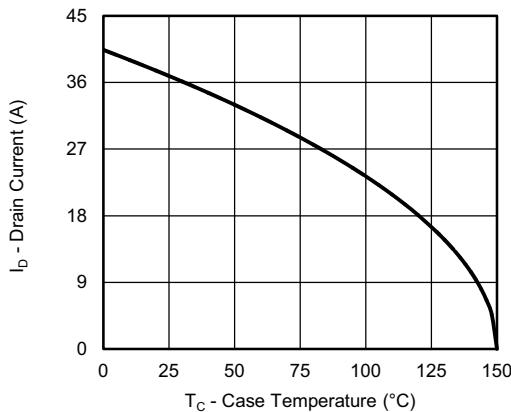
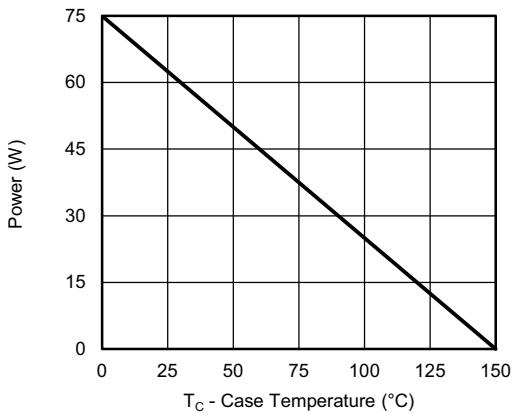
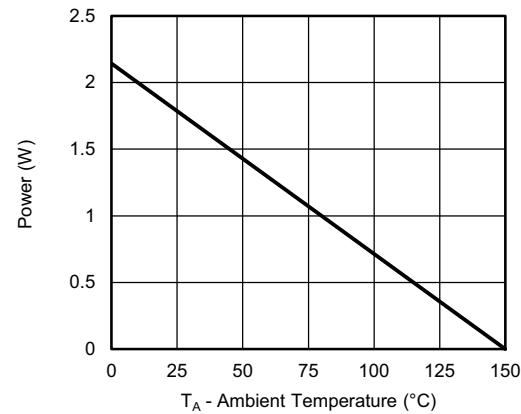
On-Resistance vs. Gate-to-Source Voltage



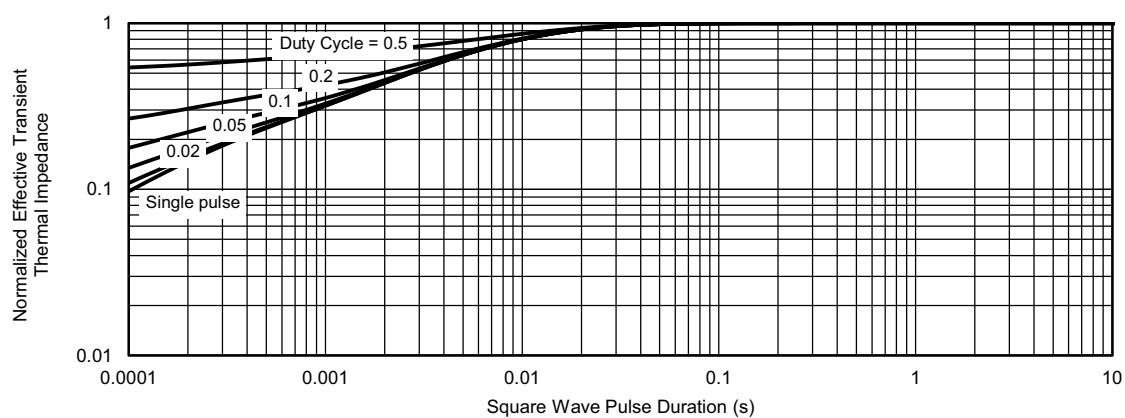
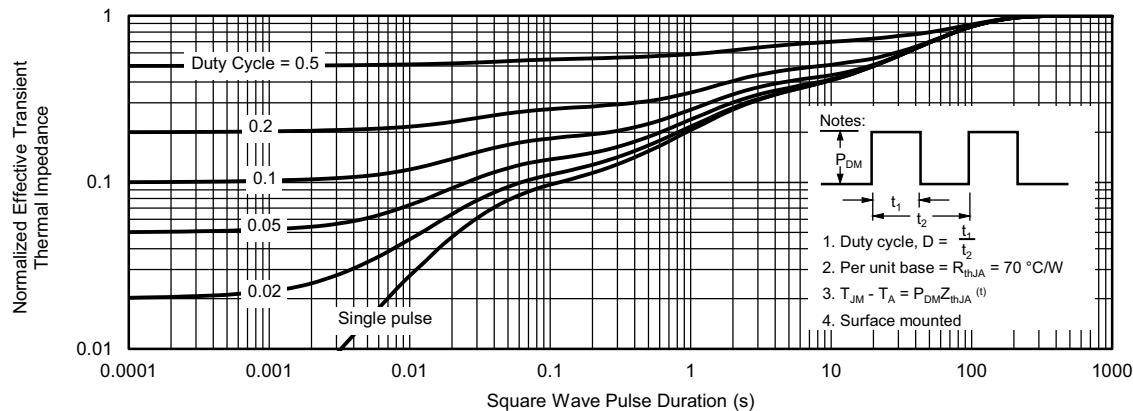
Single Pulse Power, Junction-to-Ambient



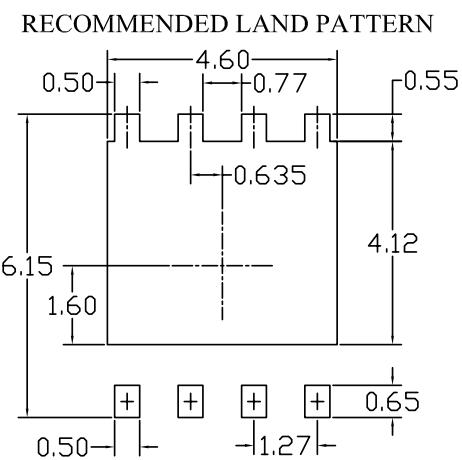
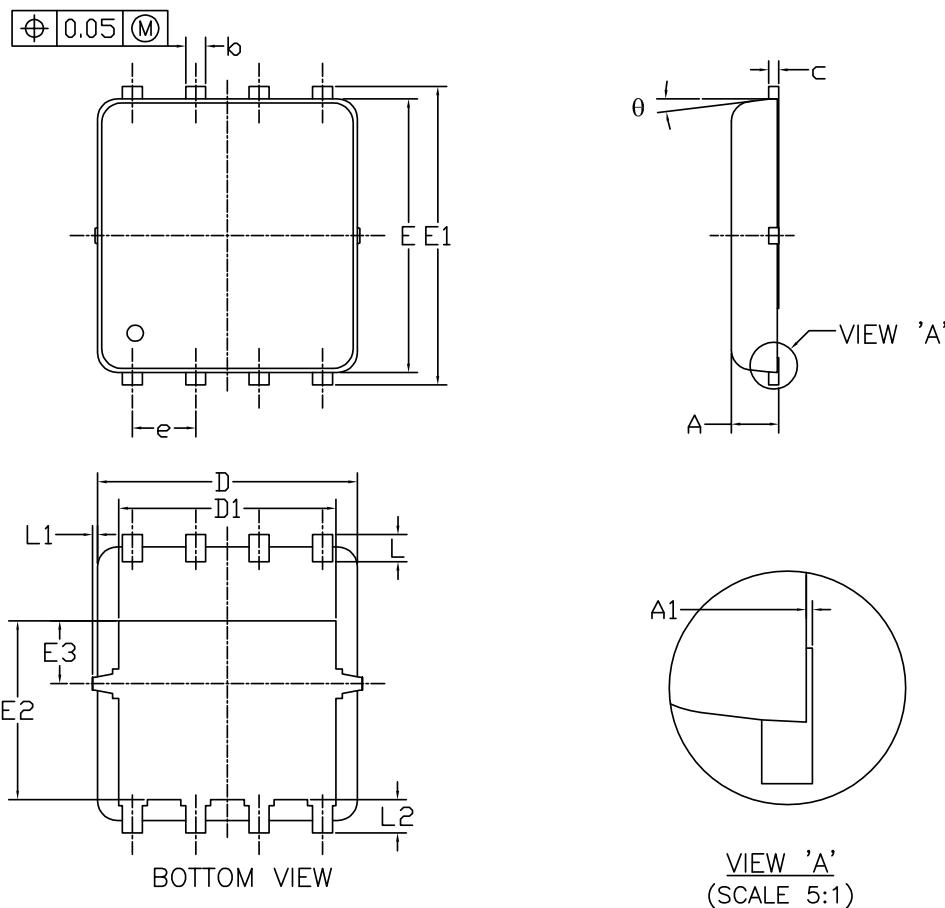
Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**

**Power, Junction-to-Ambient**
**Note**

- The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


## DFN5x6\_8L\_EP1\_P PACKAGE OUTLIN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

UNIT: mm

## NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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